

Features:

- · High voltage, high speed transistor for horizontal deflection output stages of TV and CTV circuits
- Collector-Emitter Sustaining Voltage V_{CEV} = 400V (Min.)
- Low Saturation Voltage V_{CE(sat)} = 1V (Max.) at I_C = 5A
 Fast Switching Speed: t_f = 0.75µs (Max.)

Maximum Ratings

Characteristic	Symbol	BU406	Unit	
Collector-Emitter Voltage	V _{CEO}	200		
Collector-Emitter Voltage	V _{CEV}	- 400 V		
Collector-Base Voltage	V _{CBO}			
Emitter-Base Voltage	V _{EBO}			
Collector Current-Continuous -Peak	I _C	7 10	А	
Base Current-Continuous	I _B	4	- •	
Total Power Dissipation at T _C = 25°C Derate above 25°C	P _D	60 0.48	W W/°C	
Operating and Storage Junction Temperature Range	T _J , T _{STG}	-65 to +150	°C	

Thermal Characteristics

Characteristic	Symbol	Max.	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	2.08	°C/W



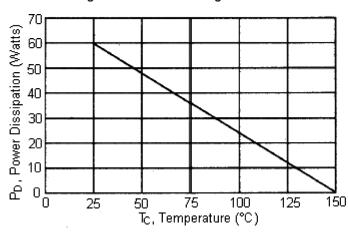


Electrical Characteristics (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min.	Max.	Unit
OFF Characteristics				
Collector-Emitter Sustaining Voltage (1) $I_C = 100 \text{mA}, I_B = 0$	V _{CEO(sus)}	200	-	V
Collector Cut off Current V _{CE} = 400V, V _{BE} = 0	I _{CES}	-	5	mA
Emitter Cut off Current $V_{EB} = 6V$, $I_{C} = 0$	I _{EBO}	-	1	μΑ
ON Characteristics (1)				
DC Current Gain $I_C = 2A$, $V_{CE} = 5V$	h _{FE}	30 (Typ.)	-	1
Collector-Emitter Saturation Voltage $I_C = 5A$, $I_B = 0.5A$	V _{CE(sat)}	-	1	V
Base-Emitter Saturation Voltage $I_C = 5A$, $I_B = 0.5A$	V _{BE(sat)}	-	1.2	
Dynamic Characteristics				
Current Gain-Bandwidth Product $I_C = 0.5A, V_{CE} = 10V, f = 1MHz$	f _T	10	-	MHz
Output Capacitance $V_{CE} = 10V$, $I_{E} = 0$, $f = 1MHz$	C _{ob}	80 (Typ.)	1	pF
Switching Characteristics				
Fall Time $V_{CC} = 40V$, $I_{C} = 5A$, $I_{B1} = -I_{B2} = 0.6A$, $L = 150\mu H$	t _f	-	0.75	μs

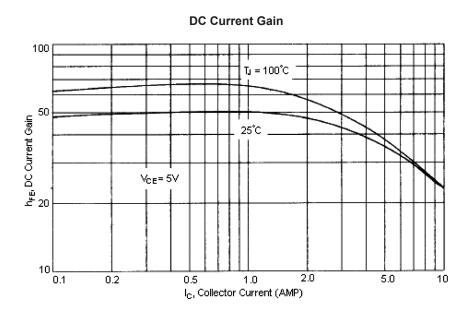
⁽¹⁾ Pulse Test: Pulse Width = 300µs, Duty Cycle ≤2%

Figure - 1 Power Derating

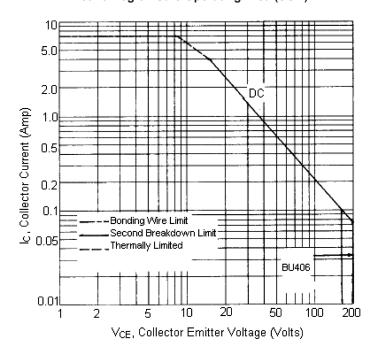








Active-Region Safe Operating Area (SOA)

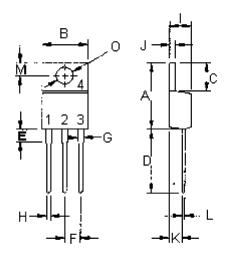


There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate $I_{C^{-}}V_{CE}$ limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of SOA curve is based on $T_{J(PK)} = 150^{\circ}C$; T_{C} is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(PK)} \leq 150^{\circ}C$. At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.







Pin Configuration:

- 1. Base
- 2. Collector
- 3. Emitter
- 4. Collector(Case)

Dimensions	Min.	Max.
Α	14.68	15.31
В	9.78	10.42
С	5.01	6.52
D	13.06	14.62
E	3.57	4.07
F	2.42	3.66
G	1.12	1.36
Н	0.72	0.96
1	4.22	4.98
J	1.14	1.38
K	2.2	2.97
L	0.33	0.55
M	2.48	2.98
0	3.7	3.9

Dimensions: Millimetres

Part Number Table

Description	Part Number	
Transistor, NPN, TO-220	BU406	

Important Notice: This data sheet and its contents (the "Information") belong to the members of the AVNET group of companies (the "Group") or are licensed to it. No licence is granted for the use of it other than for information purposes in connection with the products to which it relates. No licence of any intellectual property rights is granted. The Information is subject to change without notice and replaces all data sheets previously supplied. The Information supplied is believed to be accurate but the Group assumes no responsibility for its accuracy or completeness, any error in or omission from it or for any use made of it. Users of this data sheet should check for themselves the Information and the suitability of the products for their purpose and not make any assumptions based on information included or omitted. Liability for loss or damage resulting from any reliance on the Information or use of it (including liability resulting from negligence or where the Group was aware of the possibility of such loss or damage arising) is excluded. This will not operate to limit or restrict the Group's liability for death or personal injury resulting from its negligence. Multicomp Pro is the registered trademark of Premier Farnell Limited 2019.

